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# **A Reliable Higher Power ArF Laser with Advanced Functionality for Immersion Lithography**

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**Gigaphoton Inc.**



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- **Focus Drilling**
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  - ✓ **Approach for Focus Drilling by Laser Bandwidth Tuning**
  - ✓ **Requirements for Focus Drilling**
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- **ArF (Immersion/Dry) Roadmap**
  
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### ➤ **ArF (Immersion/Dry) Roadmap**

### ➤ **Summary**

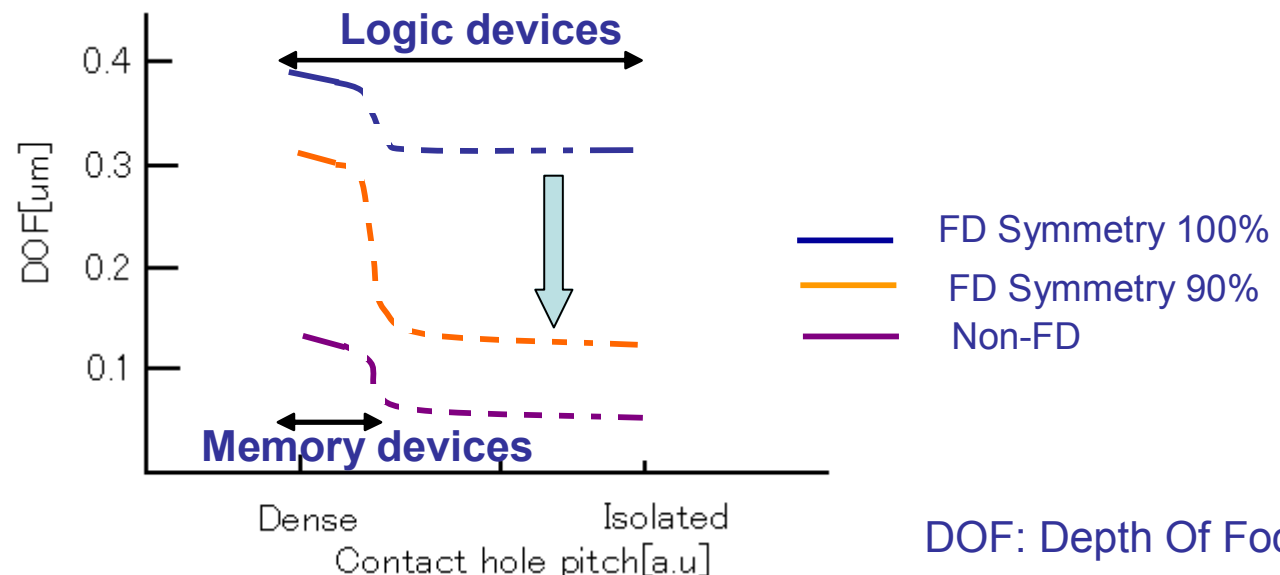
# Issue of the Exposure Process

## ➤ Lithographic Issue

- ✓ Rapid miniaturization of ULSI patterns resulting in:
- ✓ Significant DOF erosion in isolated patterns, especially in contact hole layers

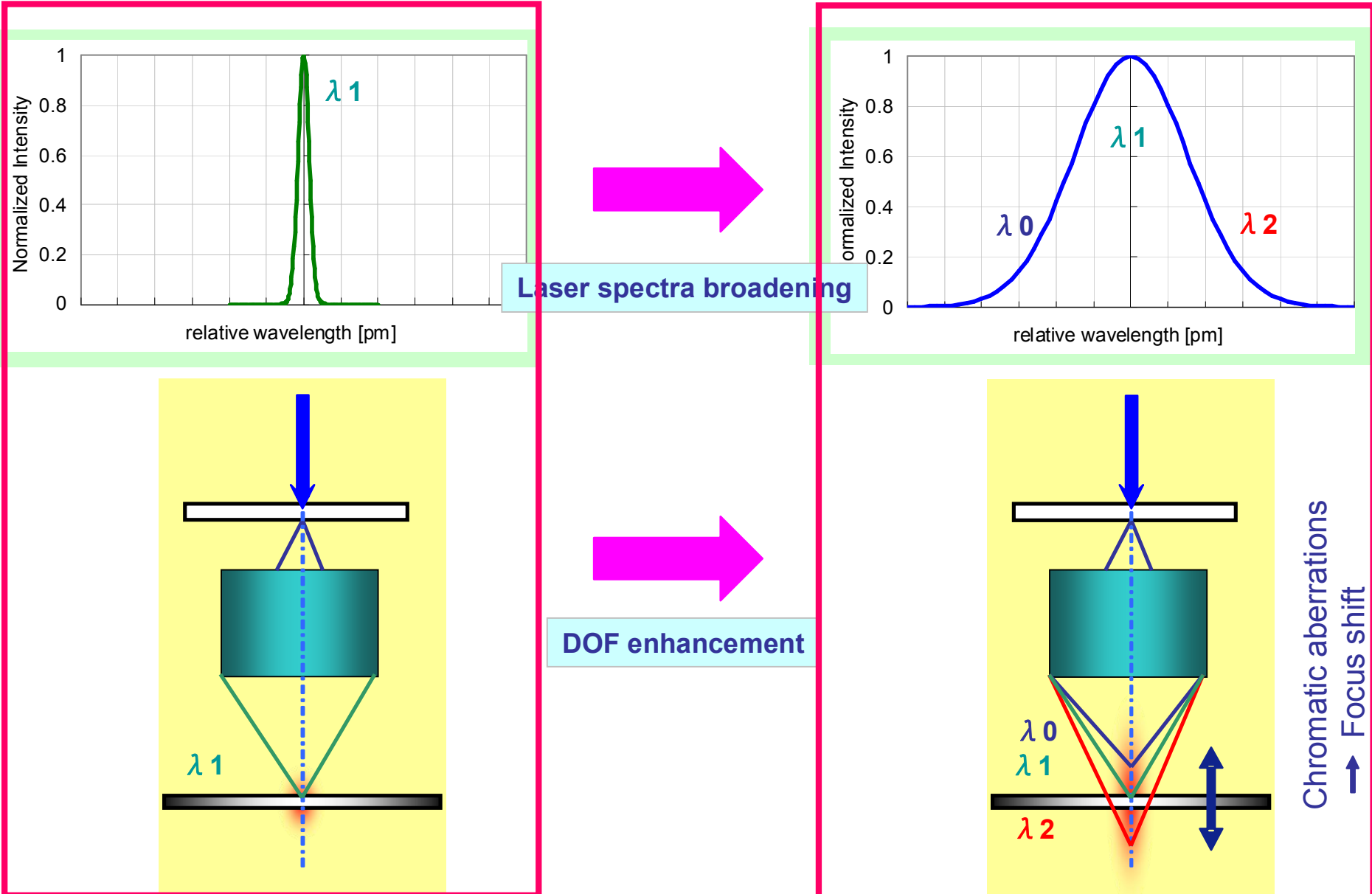
## ➤ Solution: GPI's focus drilling by laser bandwidth tuning

- ✓ Sufficient focus margin for isolated features as well as dense features
- ✓ Enabled by its unique technology to maintain spectral symmetry high



DOF: Depth Of Focus

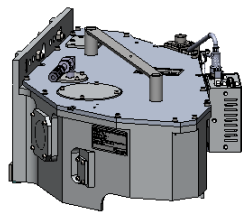
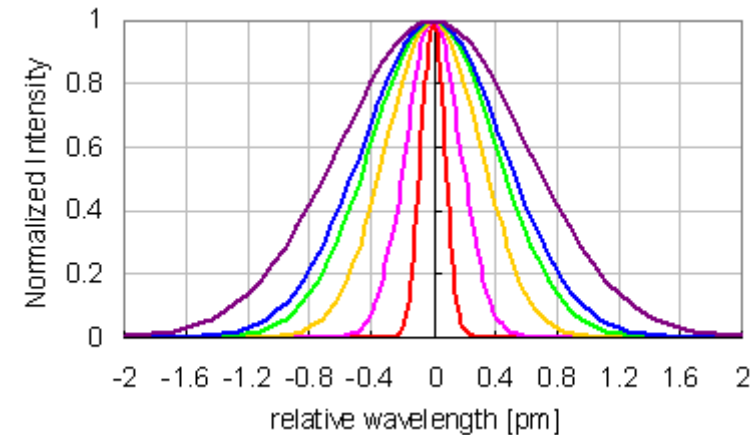
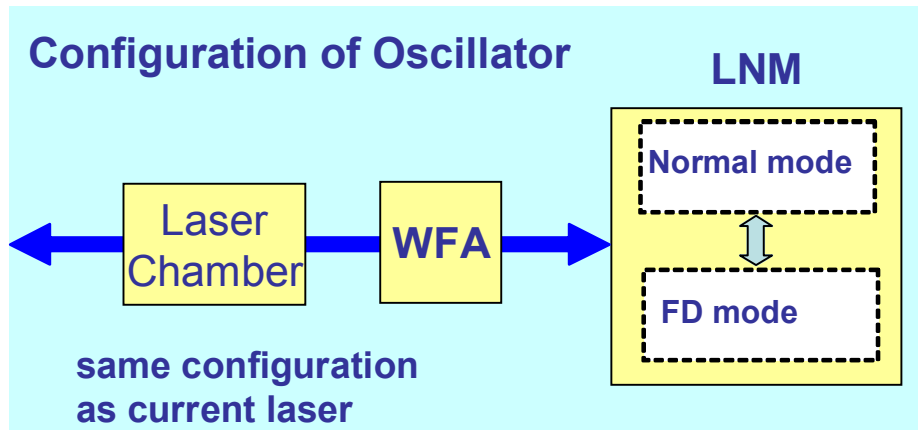
# Approach for Focus Drilling by Laser Bandwidth Tuning



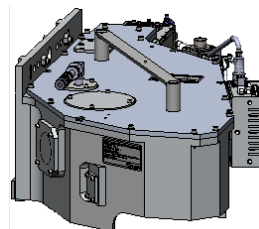
## Approach for Focus Drilling by Laser Bandwidth Tuning

### ➤ New LNM has been developed for focus drilling

- ✓ Normal mode is switched to FD (Focus Drilling) mode to broaden the spectral bandwidth.



Current LNM  
 (Only Normal mode)



New LNM for Normal /FD mode

WFA : Wave Front Adjuster  
 LNM : Line Narrow Module

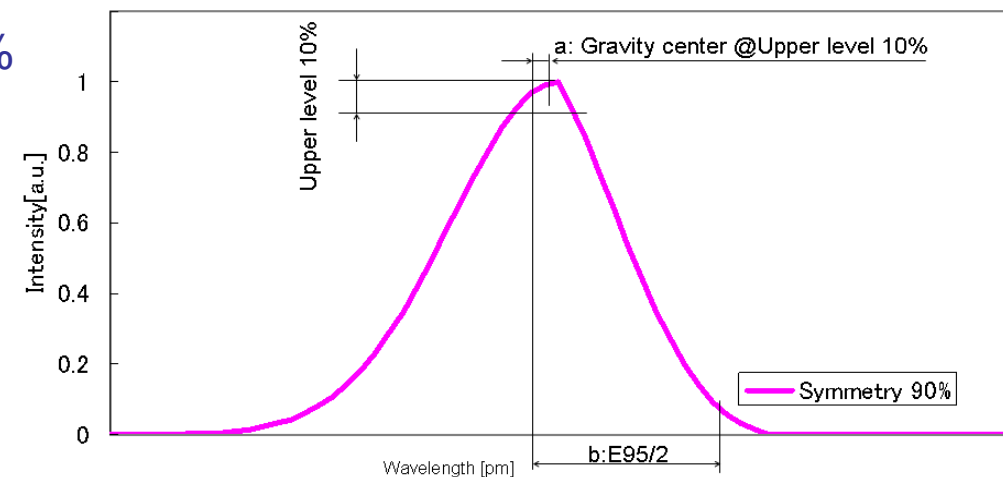
# Requirements for Focus Drilling

## ➤ Focus drilling requirements based on simulation

Item	Target value
<b>Spectrum bandwidth(E95)</b>	<b>0.3 - 2.4pm</b>
<b>Symmetry of the spectrum</b> <b>For Isolated pattern</b> <b>@DOF &gt;0.2um</b>	<b>&gt;95%</b>

## ➤ Definition of the symmetry

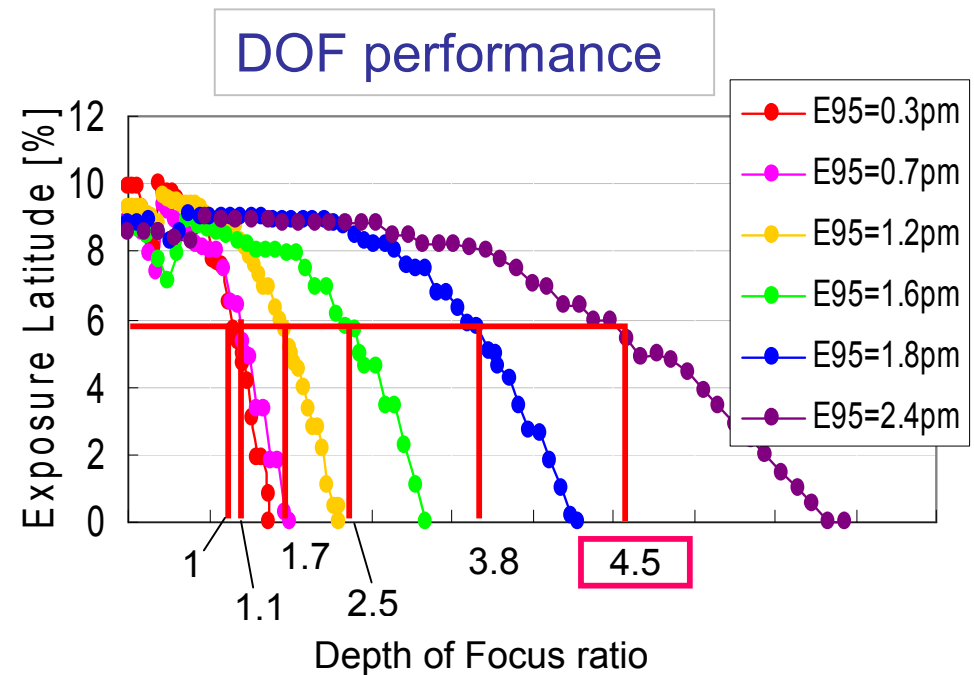
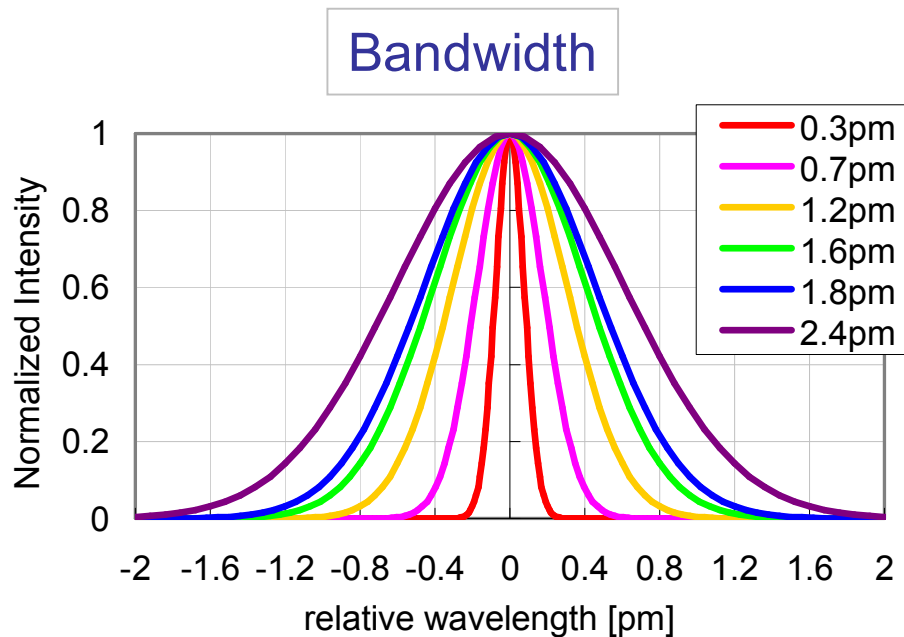
$$\text{Symmetry}[\%] = (1 - |a / b|) \times 100$$
 a : Gravity center of Upper level 10%  
 b : Spectrum width E95/2



# Requirements for Focus Drilling

## ➤ Spectral bandwidth by the simulation

- ✓ DOF can be broadened by tuning spectral bandwidth.
- ✓ 4.5 times larger DOF at E95 = 2.4  $\mu\text{m}$  compared to E95 = 0.3  $\mu\text{m}$

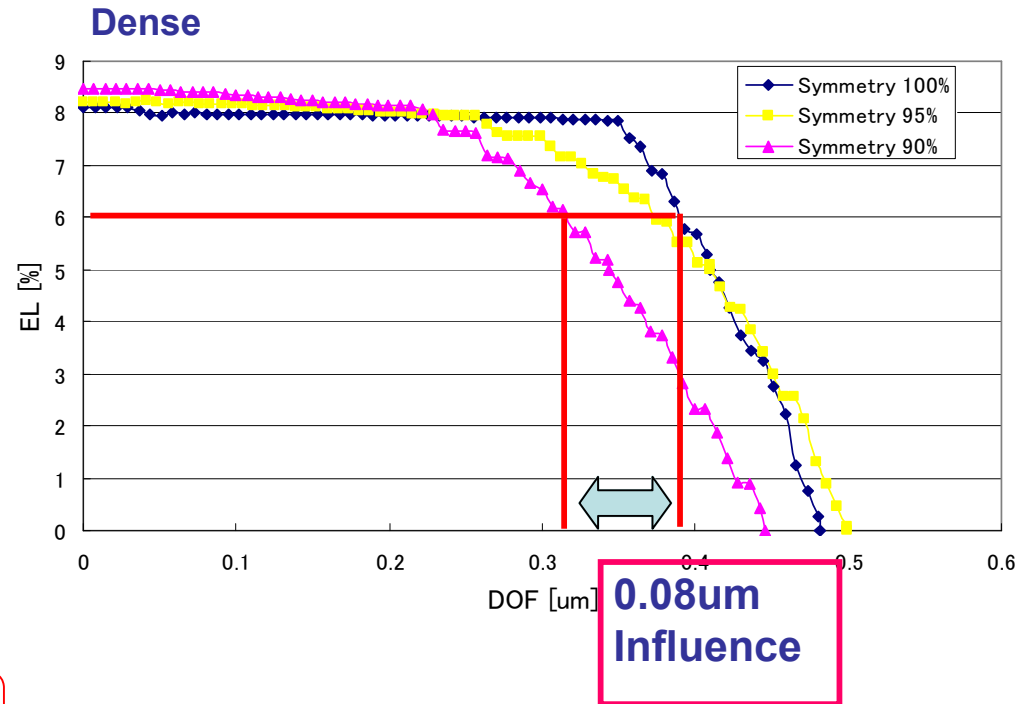
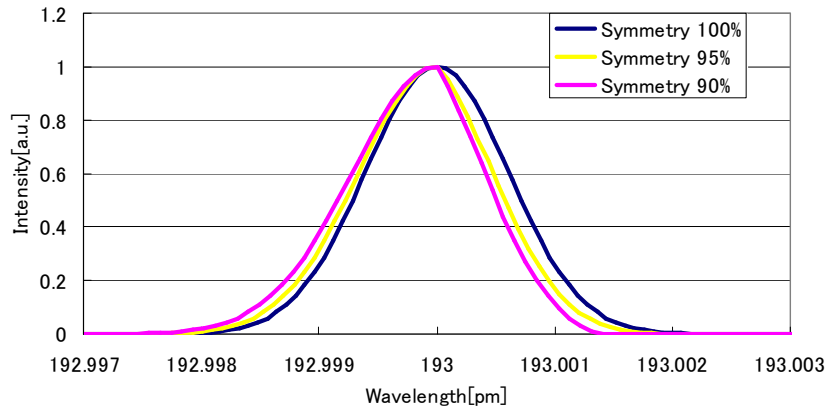




# Requirements for Focus Drilling

## ➤ Simulation for the spectral symmetry (Dense features)

### Spectrum shape



Symmetry 100%: DOF 0.39um  
 Symmetry 95% : DOF 0.38um  
 Symmetry 90% : DOF 0.31um

**Difference : 0.08um @ EL=6%**

### Conditions:

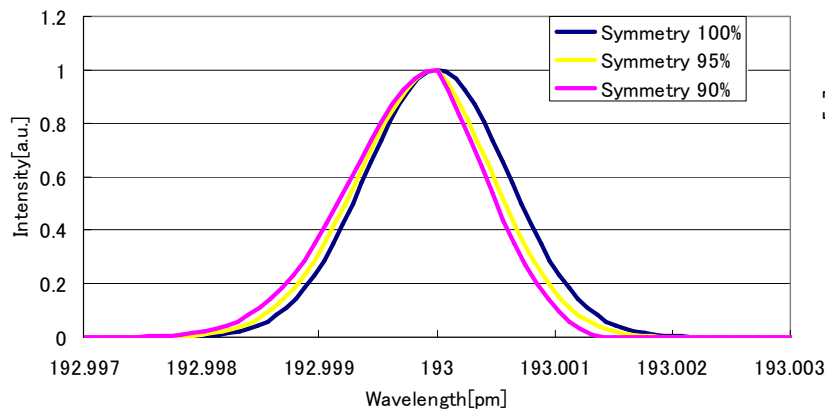
Illumination shape  
 Numerical Aperture  
 Spectrum E95  
 Dense patterns

Annular  
 1.2  
 2.4 pm (all symmetry) ≅ CBW1.7  
 Diameter/Pitch = 80 um / 160 um

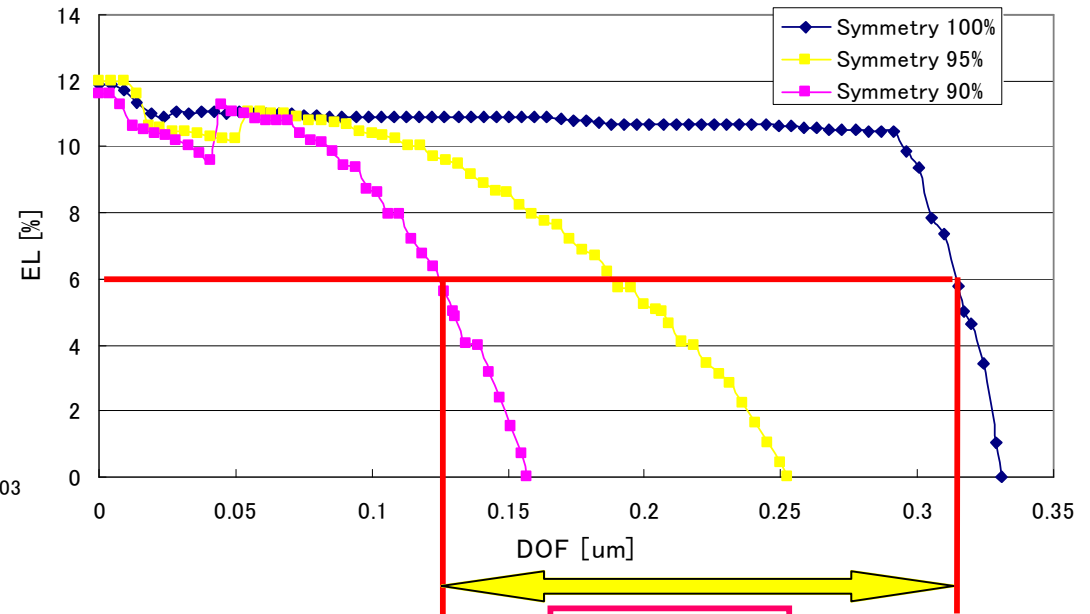
# Requirements for Focus Drilling

## ➤ Simulation for the spectral symmetry (Isolated features)

Spectrum shape



Isolated



Symmetry 100% : 0.31um  
 Symmetry 95% : 0.19um  
 Symmetry 90% : 0.12um

**Difference : 0.19 um @ EL=6%**

**0.19um  
 Influence**

**Isolated / Dense =  
 0.19 / 0.08 um = 2.4**

Conditions:  
 Illumination shape  
 Numerical Aperture  
 Spectrum E95  
 Dense patterns

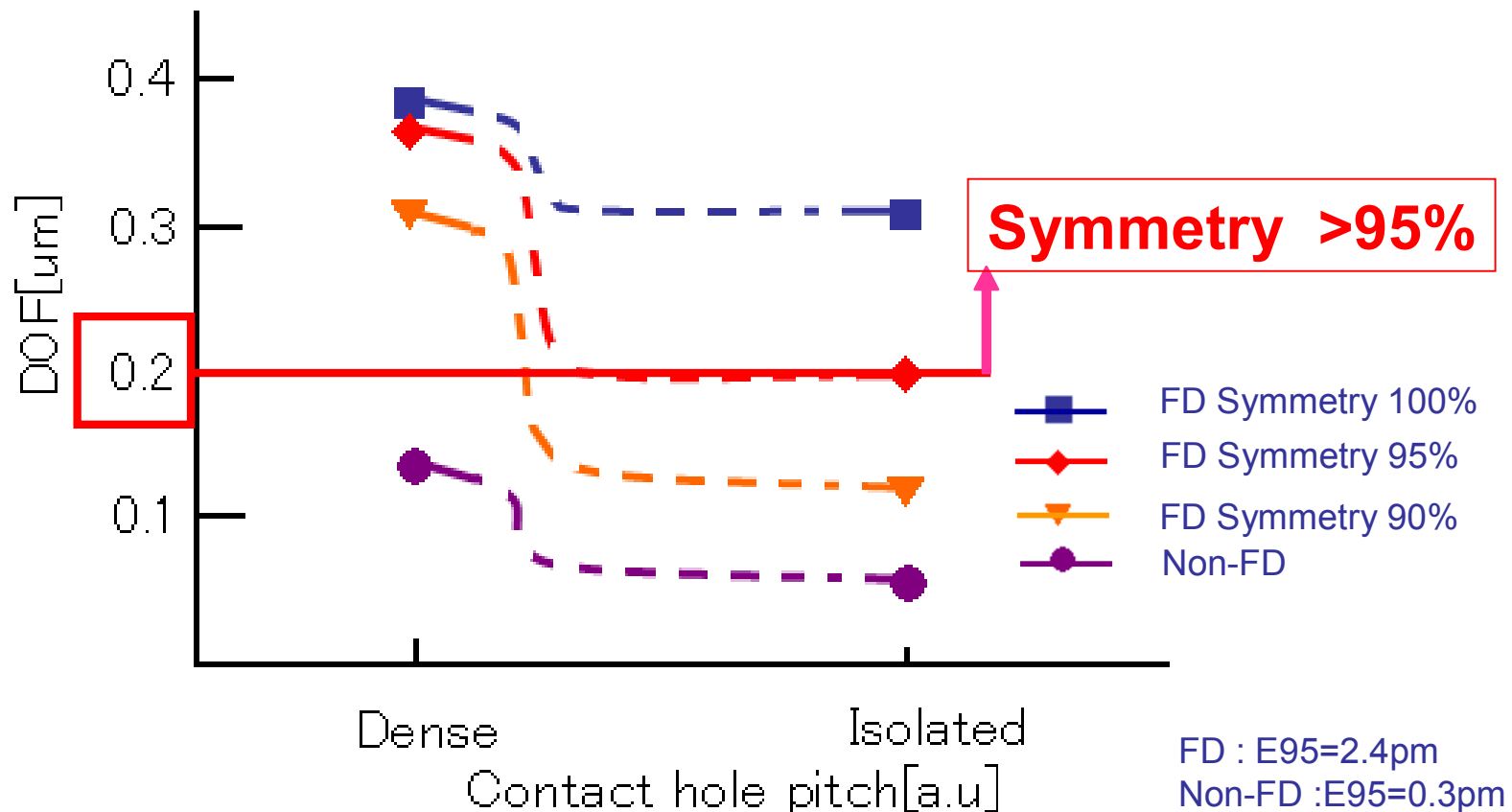
Annular  
 1.2  
 2.4 pm (all symmetry) ÷ CBW1.7  
 Diameter/Pitch = 80 um / 720 um

## Requirements for Focus Drilling

### ➤ The simulation result of the symmetry

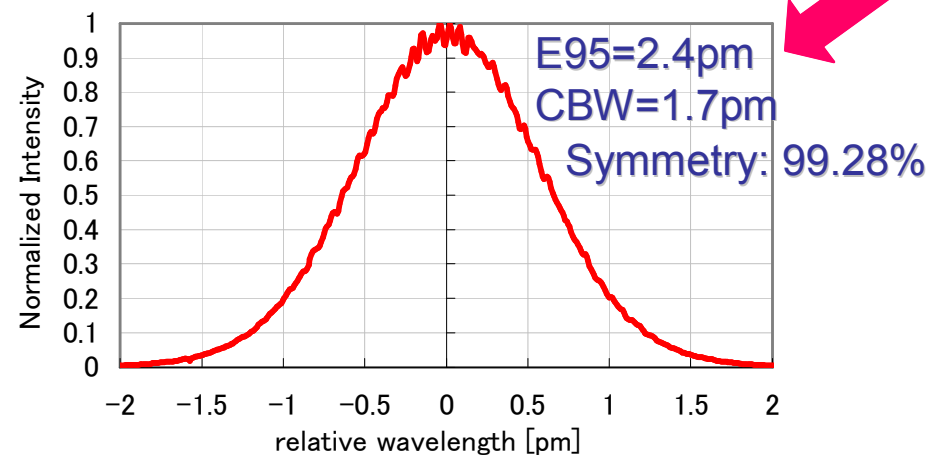
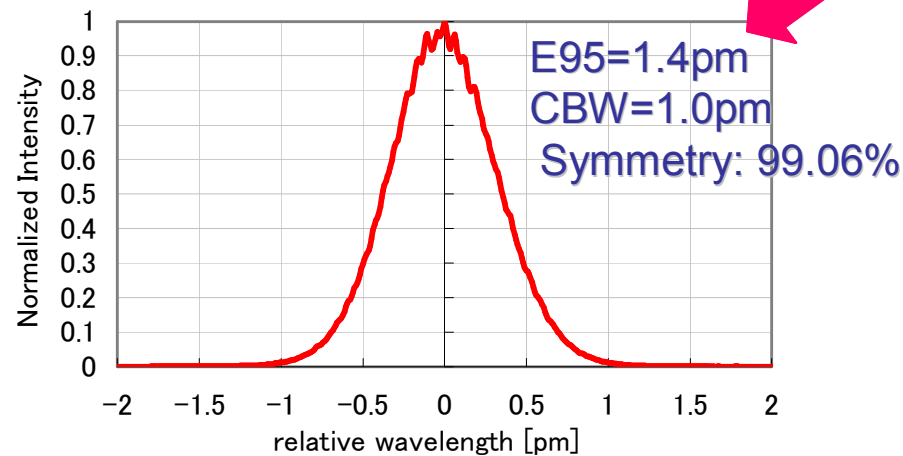
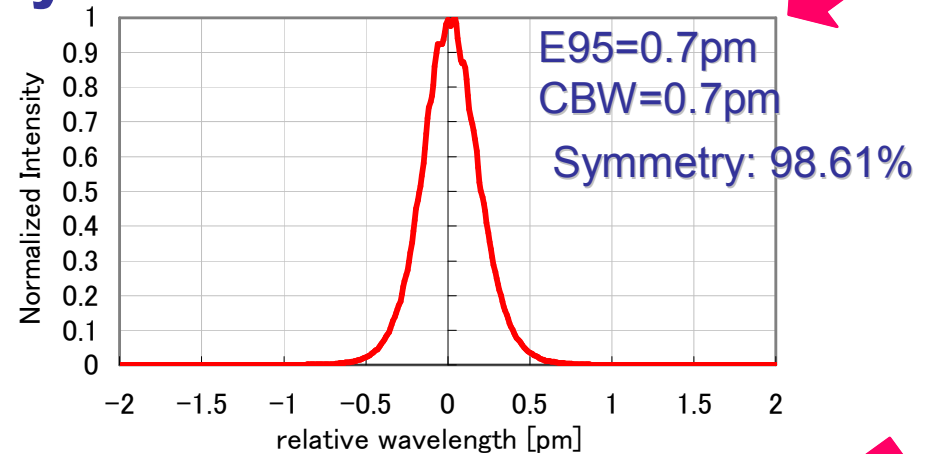
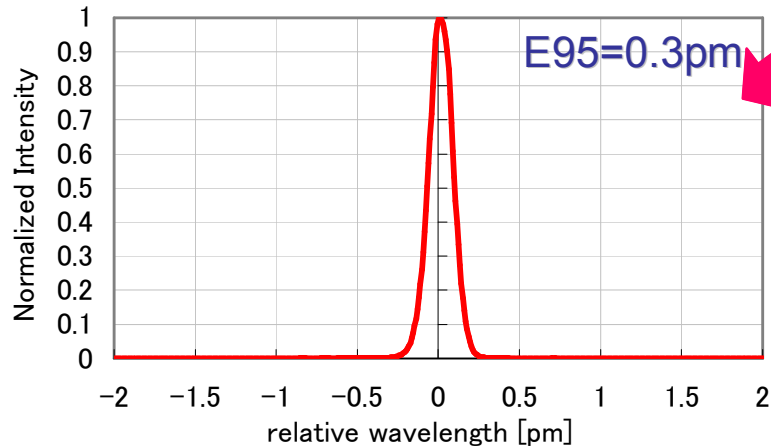
- ✓ The spectral symmetry impacts DOF.
- ✓ The more symmetric = larger DOF

### ➤➤ **0.2 um DOF = >95% symmetry needed for spectrum**



# Measurement data : Spectral Bandwidth

➤ The bandwidth is broadened by the new LNM



**CBW : Convolved bandwidth**

Ref: Proc. SPIE Optical Microlithography XXIV 7973, 28

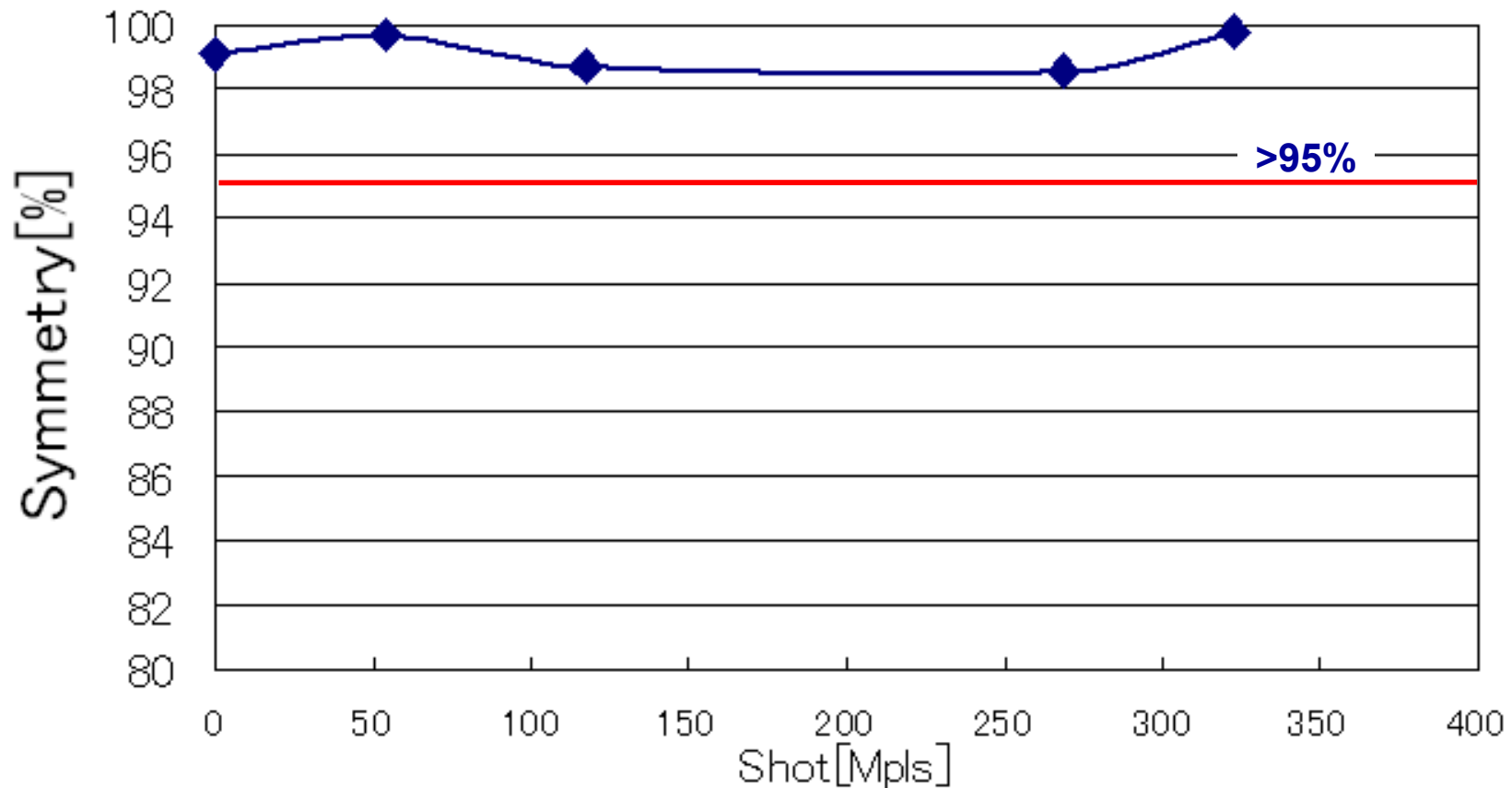
“Focus Drilling for Increased Process Latitude in High-NA Immersion Lithography”

## Measurement data : The Spectral Symmetry –Middle Term

**The spectral symmetry is stable for 330 million pulses (3 days)**

✓ Symmetry : Worst : 98.5%

Average : 99.2% stability : +/-0.64%



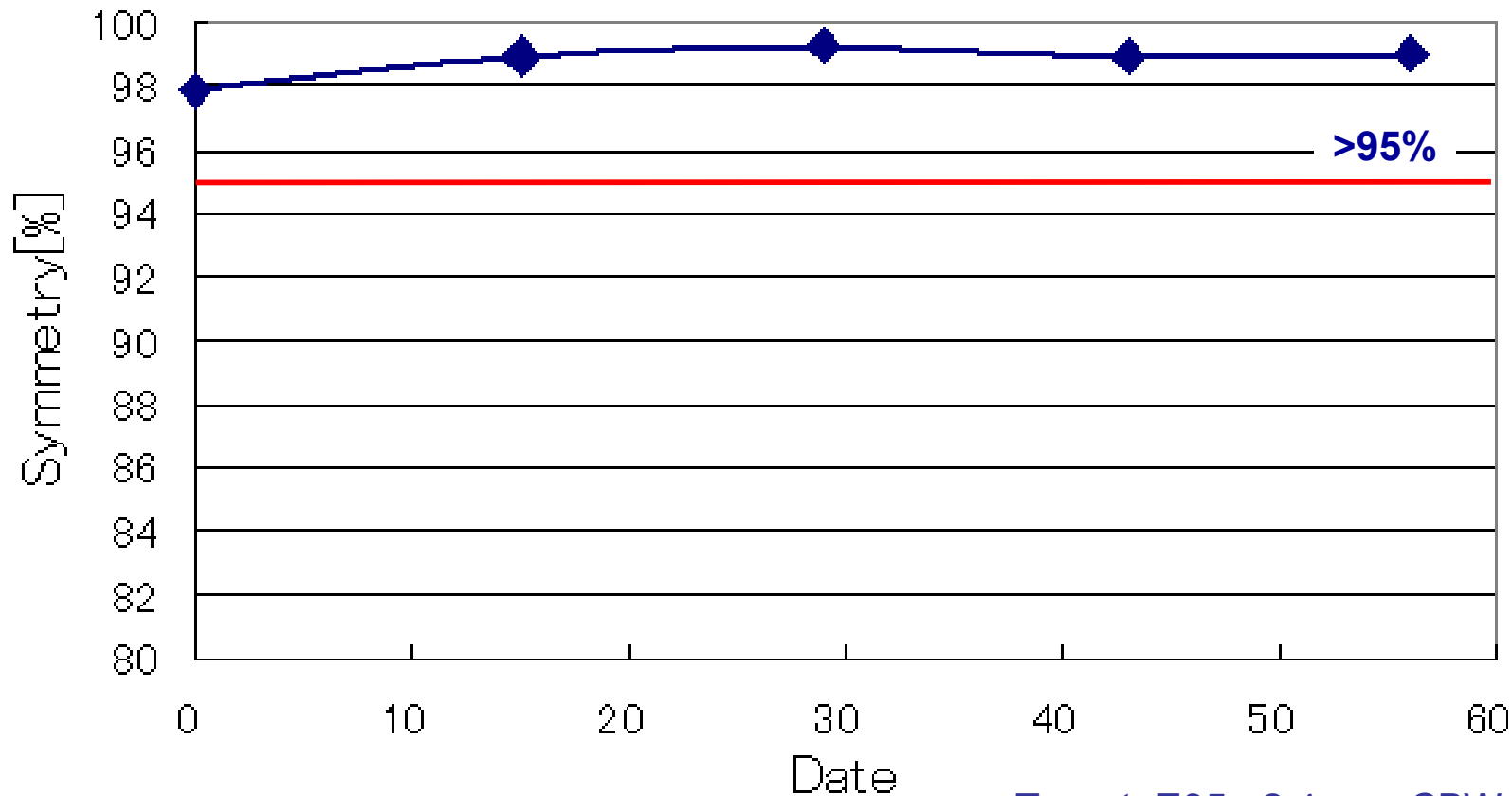
Target E95 :2.4pm =CBW:1.7 pm

## Measurement data : The Spectral Symmetry - Long Term

➤ **The spectral symmetry is stable over 50 days.**

✓ Symmetry Worst : 97.8%

Average : 98.7% stability:  $\pm 0.93\%$



Target E95 :2.4pm =CBW:1.7 pm

## Measurement data : Spectral Bandwidth / Symmetry

### ➤ Summary of the measurement result

Item	Target value	Result	Judge
<b>Spectrum bandwidth(E95)</b>	<b>0.3 to 2.4pm</b>	<b>0.3 to 2.4pm</b>	<b>OK</b>
<b>Symmetry of the spectrum For Isolated pattern</b>	<b>&gt;95%</b>	<b>97.8 to 99.7%</b>	<b>OK</b>

### ➤ The actual performances meet the design target



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## Field data

### ➤ Report of the actual exposure result in the field

✓ DOF changes when change a spectrum (CBW)

✓ Confirmed proximity matching

✓ Process window

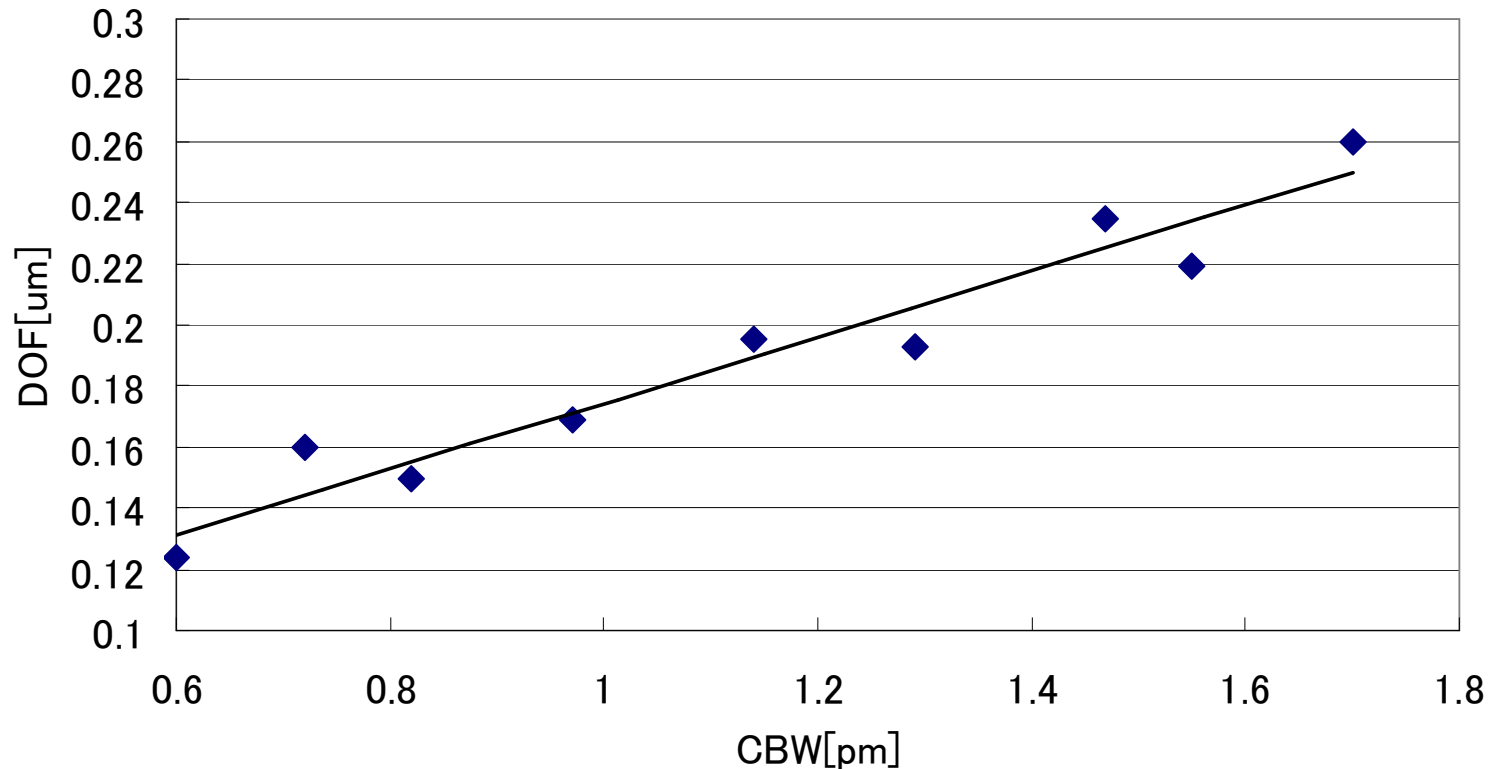
✓ Critical Dimension (CD)

EFESE\_HR is ASML's product name (GPI Focus drilling function by bandwidth tuning)

EFESE\_Rx is ASML's product name (ASML Focus drilling function by stage tilt )

# Field data : Actual exposure result Expand DOF

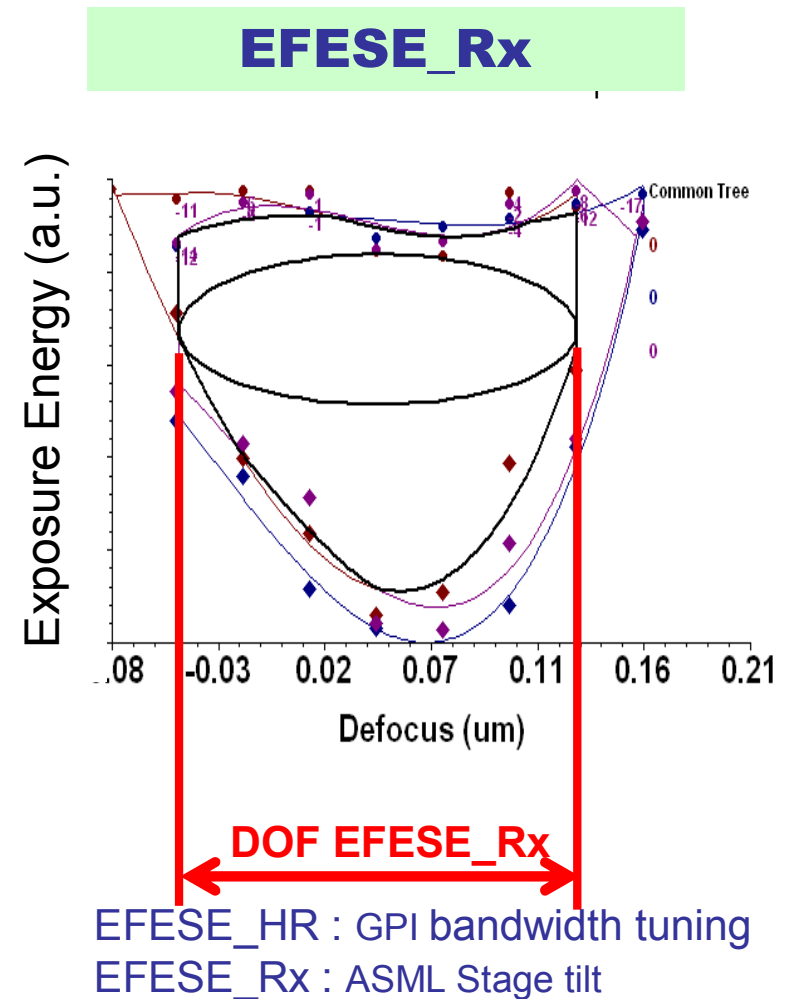
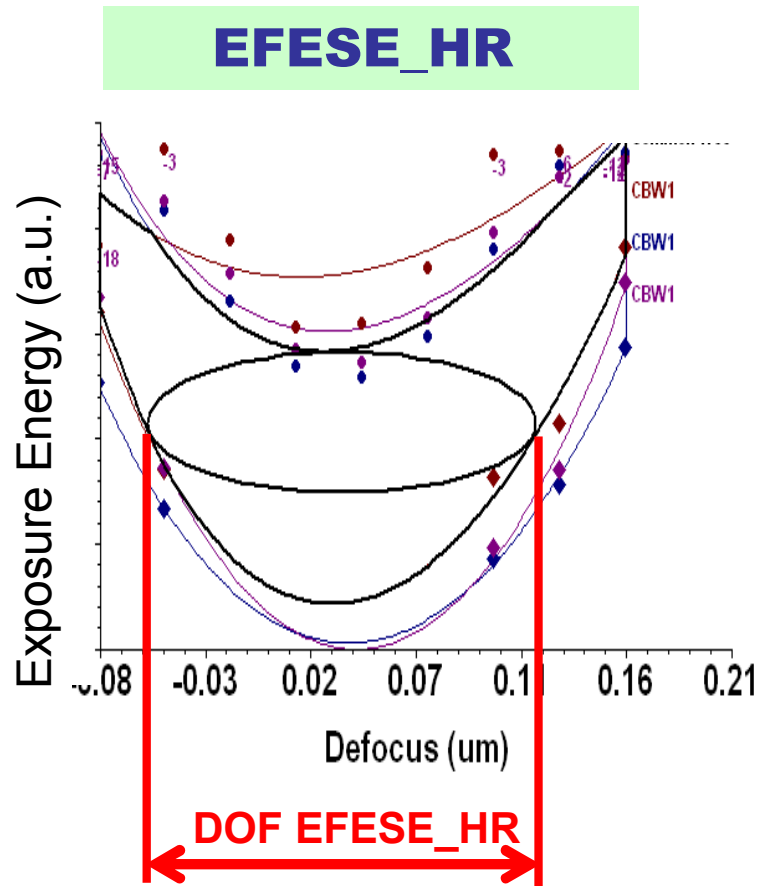
## The increase of DOF with CBW



- The analysis of Focus-Exposure-Matrix (FEM) wafers exposed at different CBW values has been performed for the semi-iso with
  - target CD of 85 nm,
  - pitch=365 nm
  - annular illumination settings with NA=1.2

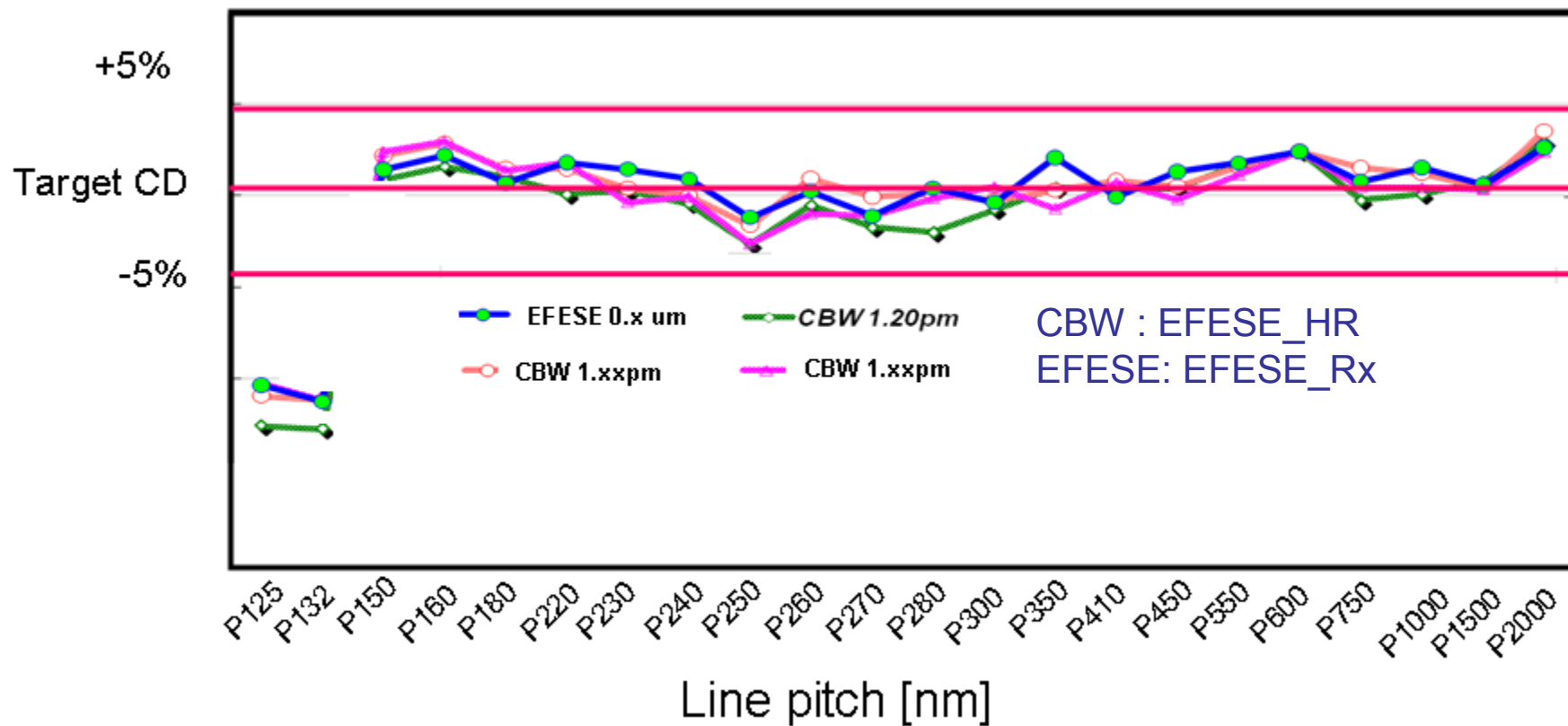
## Field data: Process window

➤ **DOF by EFESE\_HR is substantially same as that by EFESE\_Rx.**



## Field data: Critical Dimension(CD)

- Line pitches by EFESE\_HR are substantially the same as those by EFESE\_Rx .



CD : Process less than 80 nm

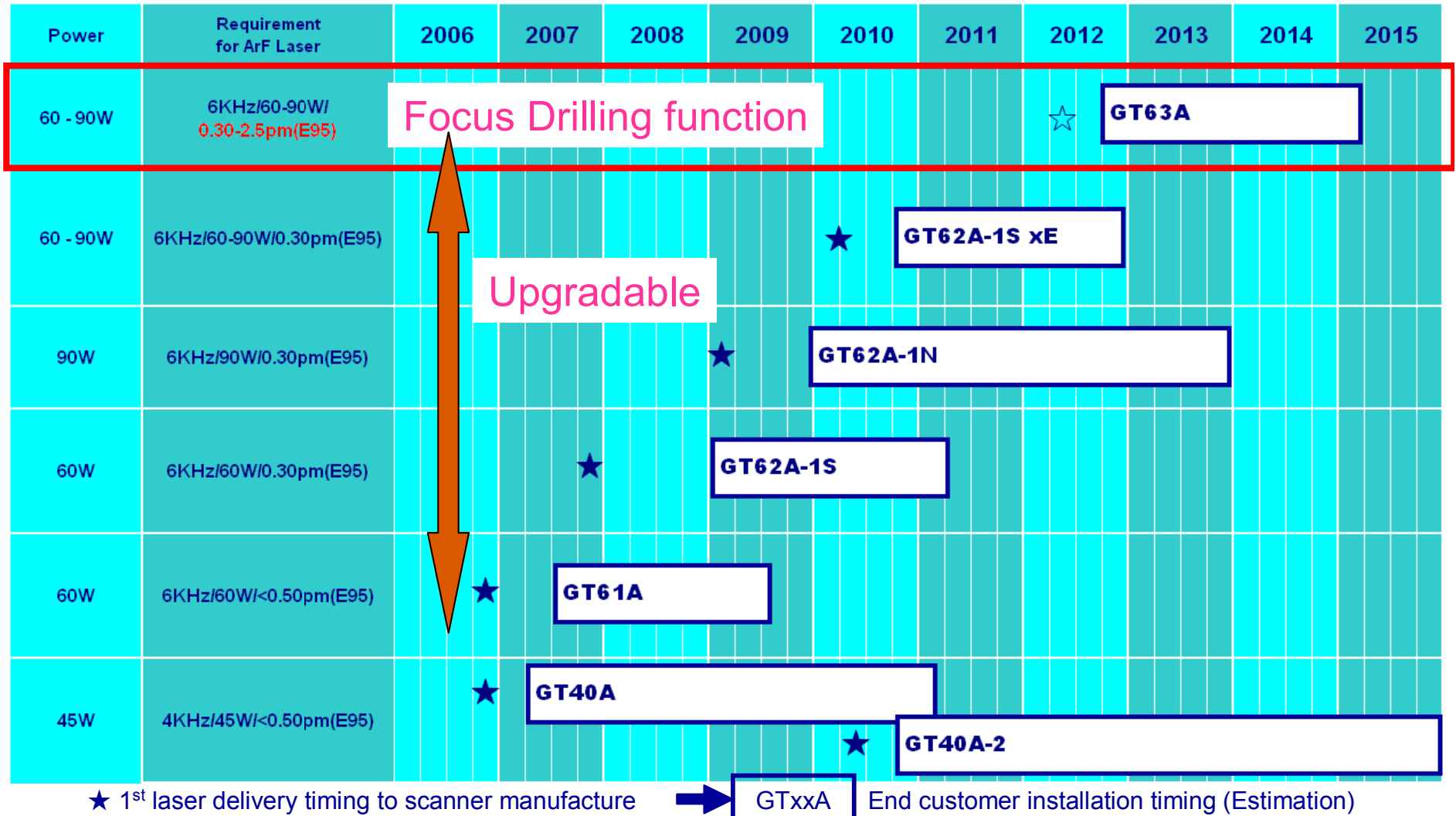
EFESE\_HR : GPI bandwidth tuning  
 EFESE\_Rx : ASML Stage tilt



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# ArF (Immersion/Dry) Roadmap



***New product***

## ArF (Immersion/Dry) Roadmap GPI will release new ArF laser GT63A



### ➤ **GT63A**

- ✓ **Based on GT62A-1SxE**

### ➤ **Features**

#### ✓ **New functionality and benefit**

- Focus drilling LNM\* : Enable FD
- Gas refill free : Shorter downtime
- 60B pulse New Laser chamber : Lower cost & Shorter downtime
- New Monitoring : Higher reliability (REDeeM piece, FDC)

### ➤ **First shipment of GT63A**

- ✓ **Q2 2012 to litho tool manufacturer (TBD)**

### ➤ **New development HW and SW are applicable to install base lasers**

- ✓ **GT61A / GT62A-1S / GT62A-1SxE**

\* LNM hardware is not standard.  
 It is commercial option



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## Summary

### ➤ Focus drilling

- ✓ DOF enhancement by laser spectrum broadening
  - ✓ Symmetry is the key for isolated features
- ✓ GPI's new technology offers DOF enhancement with very high symmetric spectrum, with stability verified for middle and long term
- ✓ The solution has been verified to be equivalent to stage tilting solution(EFESE\_Rx) under chip making environment

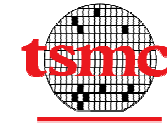
### ➤ ArF (Immersion/Dry) roadmap

- ✓ Focus Drilling function is commercial option for GT63A.
- ✓ Applicable for existing product lines down to GT61A

## Acknowledgement

Special thanks to:

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Miranda Un, Eric Chen



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**Thank you for your kind attention !**

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